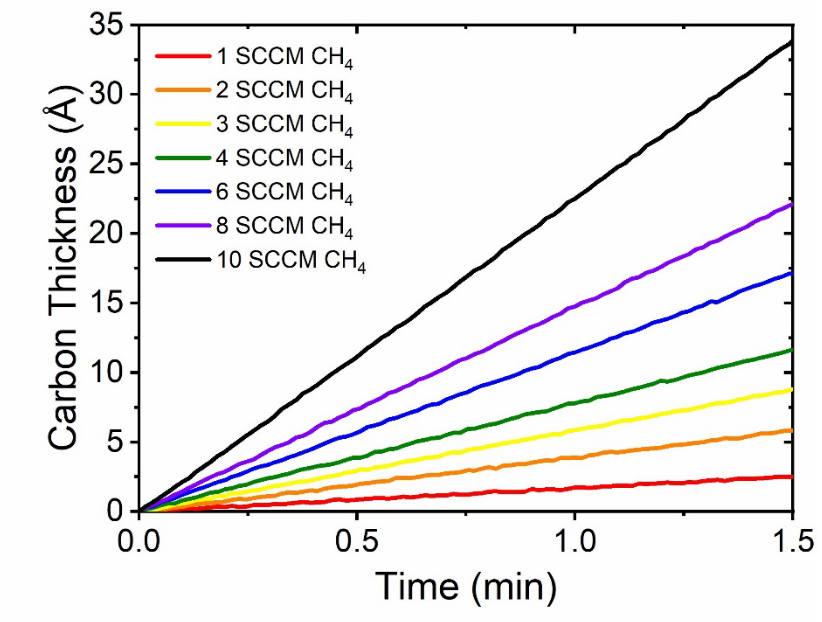

Figure 1. Deposition of carbon films using EE-CVD at 0 V applied sample bias. Deposition rate increases linearly with increasing CH_4 flowrate between 1 and 10 SCCM CH_4.

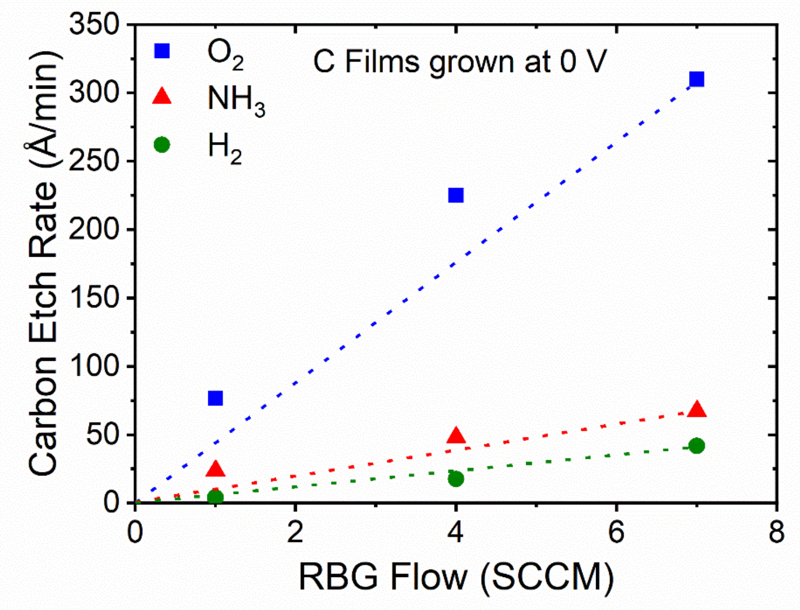

Figure 2. Etch rates of carbon films grown at 0 V applied sample bias for various RBG flowrates. Etching was conducted using a -30 V applied sample bias. Etch rates increased with increasing RBG flowrates. O_2 displayed the highest etch rate, while NH_3 and H_2 displayed lower etch rates.